M Pepper

List of Publications by Year in descending order

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615 papers	26,092 citations	14644 66 h-index	8852 145 g-index
618 all docs	618 docs citations	618 times ranked	10984 citing authors

#	Article	IF	Citations
1	New Method for High-Accuracy Determination of the Fine-Structure Constant Based on Quantized Hall Resistance. Physical Review Letters, 1980, 45, 494-497.	2.9	5,601
2	One-dimensional transport and the quantisation of the ballistic resistance. Journal of Physics C: Solid State Physics, 1988, 21, L209-L214.	1.5	1,885
3	Possible Spin Polarization in a One-Dimensional Electron Gas. Physical Review Letters, 1996, 77, 135-138.	2.9	657
4	One-Dimensional Conduction in the 2D Electron Gas of a GaAs-AlGaAs Heterojunction. Physical Review Letters, 1986, 56, 1198-1201.	2.9	594
5	Measurements of Coulomb blockade with a noninvasive voltage probe. Physical Review Letters, 1993, 70, 1311-1314.	2.9	535
6	In vivostudy of human skin using pulsed terahertz radiation. Physics in Medicine and Biology, 2004, 49, 1595-1607.	1.6	430
7	Terahertz Frequency Sensing and Imaging: A Time of Reckoning Future Applications?. Proceedings of the IEEE, 2005, 93, 1722-1743.	16.4	370
8	Gigahertz quantized charge pumping. Nature Physics, 2007, 3, 343-347.	6.5	363
9	Magnetic Depopulation of 1D Subbands in a Narrow 2D Electron Gas in a GaAs:AlGaAs Heterojunction. Physical Review Letters, 1986, 57, 1769-1772.	2.9	342
10	All-electric all-semiconductor spin field-effect transistors. Nature Nanotechnology, 2015, 10, 35-39.	15.6	289
11	Using terahertz pulse spectroscopy to study the crystalline structure of a drug: A case study of the polymorphs of ranitidine hydrochloride. Journal of Pharmaceutical Sciences, 2003, 92, 831-838.	1.6	285
12	Terahertz pulsed imaging of skin cancer in the time and frequency domain. Journal of Biological Physics, 2003, 29, 257-259.	0.7	274
13	High-frequency single-electron transport in a quasi-one-dimensional GaAs channel induced by surface acoustic waves. Journal of Physics Condensed Matter, 1996, 8, L531-L539.	0.7	256
14	Metal-Insulator Transition atB=0in a Dilute Two Dimensional GaAs-AlGaAs Hole Gas. Physical Review Letters, 1998, 80, 1292-1295.	2.9	233
15	Interaction effects in a one-dimensional constriction. Physical Review B, 1998, 58, 4846-4852.	1.1	221
16	Single-electron transport in a one-dimensional channel by high-frequency surface acoustic waves. Physical Review B, 1997, 56, 15180-15184.	1.1	219
17	Simulation of terahertz pulse propagation in biological systems. Applied Physics Letters, 2004, 84, 2190-2192.	1.5	176
18	Evolution of half plateaus as a function of electric field in a ballistic quasi-one-dimensional constriction. Physical Review B, 1991, 44, 13549-13555.	1.1	170

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19	Spin-triplet negatively charged excitons in GaAs quantum wells. Physical Review B, 1995, 52, 7841-7844.	1.1	163
20	Addition of the one-dimensional quantised ballistic resistance. Journal of Physics C: Solid State Physics, 1988, 21, L887-L891.	1.5	158
21	Analysis of sustained-release tablet film coats using terahertz pulsed imaging. Journal of Controlled Release, 2007, 119, 253-261.	4.8	145
22	Quantum Conductance in Silicon Oxide Resistive Memory Devices. Scientific Reports, 2013, 3, 2708.	1.6	144
23	Detection of single photons using a field-effect transistor gated by a layer of quantum dots. Applied Physics Letters, 2000, 76, 3673-3675.	1.5	142
24	Drug hydrate systems and dehydration processes studied by terahertz pulsed spectroscopy. International Journal of Pharmaceutics, 2007, 334, 78-84.	2.6	134
25	The observation of interaction and localisation effects in a two-dimensional electron gas at low temperatures. Journal of Physics C: Solid State Physics, 1980, 13, L985-L993.	1.5	133
26	Four-terminal magnetoresistance of a two-dimensional electron-gas constriction in the ballistic regime. Physical Review B, 1988, 37, 8534-8536.	1.1	130
27	Magneto-optical spectroscopy of positively charged excitons in GaAs quantum wells. Physical Review B, 1995, 52, R5523-R5526.	1.1	124
28	Clock-Controlled Emission of Single-Electron Wave Packets in a Solid-State Circuit. Physical Review Letters, 2013, 111, 216807.	2.9	112
29	Quenching of excitonic optical transitions by excess electrons in GaAs quantum wells. Physical Review B, 1995, 51, 18049-18052.	1.1	110
30	Elimination of scattering effects in spectral measurement of granulated materials using terahertz pulsed spectroscopy. Applied Physics Letters, 2008, 92, .	1.5	105
31	Anomalous Coulomb Drag in Electron-Hole Bilayers. Physical Review Letters, 2008, 101, 246801.	2.9	104
32	The transition from one- to zero-dimensional ballistic transport. Journal of Physics C: Solid State Physics, 1988, 21, L893-L898.	1.5	102
33	Vanishing hall voltage in a quasi-one-dimensionalGaAsâ^'AlxGa1â^'xAsheterojunction. Physical Review B, 1988, 38, 8518-8521.	1.1	101
34	Spin properties of low-density one-dimensional wires. Physical Review B, 2000, 61, R13365-R13368.	1.1	99
35	Enhanced coherent terahertz emission from indium arsenide in the presence of a magnetic field. Applied Physics Letters, 2000, 76, 2038-2040.	1.5	98
36	Thermoelectric signature of the excitation spectrum of a quantum dot. Physical Review B, 1997, 55, R10197-R10200.	1.1	97

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37	Electrostatically defined heterojunction rings and the Aharonovâ€“Bohm effect. Applied Physics Letters, 1989, 54, 21-23.	1.5	96
38	Crosslinked PMMA as a high-resolution negative resist for electron beam lithography and applications for physics of low-dimensional structures. Semiconductor Science and Technology, 1996, 11, 1235-1238.	1.0	96
39	Weak Localization, Hole-Hole Interactions, and the â€œMetalâ€•Insulator Transition in Two Dimensions. Physical Review Letters, 2000, 84, 2489-2492.	2.9	96
40	Continuous-wave terahertz system with a 60 dB dynamic range. Applied Physics Letters, 2005, 86, 204104.	1.5	96
41	Correlation Effects on the Coupled Plasmon Modes of a Double Quantum Well. Physical Review Letters, 1997, 78, 2204-2207.	2.9	92
42	Observation of Charge Transport by Negatively Charged Excitons. Science, 2001, 294, 837-839.	6.0	88
43	Magnetotransport in a nonplanar two-dimensional electron gas. Physical Review B, 1995, 52, R8629-R8632.	1.1	86
44	Single-electron acoustic charge transport by two counterpropagating surface acoustic wave beams. Physical Review B, 1999, 60, 4850-4855.	1.1	86
45	Two-dimensional hopping conductivity in aÎ´-dopedGaAs/AlxGa1â^'xAsheterostructure. Physical Review B, 1999, 59, 4580-4583.	1.1	86
46	Hole-Hole Interaction Effect in the Conductance of the Two-Dimensional Hole Gas in the Ballistic Regime. Physical Review Letters, 2002, 89, 076406.	2.9	86
47	Conductance Quantization at a Half-Integer Plateau in a Symmetric GaAs Quantum Wire. Science, 2006, 312, 1359-1362.	6.0	85
48	Zeeman Splitting in Ballistic Hole Quantum Wires. Physical Review Letters, 2006, 97, 026403.	2.9	85
49	Logarithmic corrections to two-dimensional transport in silicon inversion layers. Journal of Physics C: Solid State Physics, 1981, 14, 5737-5762.	1.5	82
50	Magnetic delocalisation of a two-dimensional electron gas and the quantum law of electron-electron scattering. Journal of Physics C: Solid State Physics, 1981, 14, L395-L402.	1.5	82
51	Thermometer for the 2D Electron Gas using 1D Thermopower. Physical Review Letters, 1998, 81, 3491-3494.	2.9	81
52	High-frequency acousto-electric single-photon source. Physical Review A, 2000, 62, .	1.0	81
53	Empirical relation between gate voltage and electrostatic potential in the one-dimensional electron gas of a split-gate device. Physical Review B, 1989, 39, 6283-6286.	1.1	77
54	Negative magnetoresistance in the variable-range-hopping regime inn-type GaAs. Physical Review B, 1989, 39, 8059-8061.	1.1	77

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55	Ballistic transport in oneâ€dimensional constrictions formed in deep twoâ€dimensional electron gases. Applied Physics Letters, 1995, 67, 109-111.	1.5	77
56	Tunneling between two-dimensional electron gases in a strong magnetic field. Physical Review B, 1994, 50, 15465-15468.	1.1	75
57	Fano Factor Reduction on the 0.7 Conductance Structure of a Ballistic One-Dimensional Wire. Physical Review Letters, 2004, 93, 116602.	2.9	75
58	Interaction Effects at Crossings of Spin-Polarized One-Dimensional Subbands. Physical Review Letters, 2003, 91, 136404.	2.9	73
59	Controlled wave-function mixing in strongly coupled one-dimensional wires. Physical Review B, 1999, 59, 12252-12255.	1.1	72
60	Incipient Formation of an Electron Lattice in a Weakly Confined Quantum Wire. Physical Review Letters, 2009, 102, 056804.	2.9	71
61	Variable-range hopping in a silicon inversion layer. Physics Letters, Section A: General, Atomic and Solid State Physics, 1974, 47, 71-72.	0.9	70
62	Non-linear conductance of a saddle-point constriction. Journal of Physics Condensed Matter, 1992, 4, 1323-1333.	0.7	70
63	Magnetic-field-induced insulator-quantum Hall-insulator transition in a disordered two-dimensional electron gas. Journal of Physics Condensed Matter, 1994, 6, 4763-4770.	0.7	70
64	Spinâ€dependent recombination in irradiated Si/SiO2device structures. Applied Physics Letters, 1988, 52, 1161-1163.	1.5	69
65	Spin splitting of one-dimensional subbands in high quality quantum wires at zero magnetic field. Physical Review B, 2000, 62, 15842-15850.	1.1	68
66	The Aharonov-Bohm effect in electrostatically defined heterojunction rings. Journal of Physics C: Solid State Physics, 1988, 21, L325-L331.	1.5	67
67	Single-electron tunneling and Coulomb charging effects in aysmmetric double-barrier resonant-tunneling diodes. Physical Review B, 1992, 45, 14407-14410.	1.1	67
68	Screening of the surface-acoustic-wave potential by a metal gate and the quantization of the acoustoelectric current in a narrow channel. Physical Review B, 1998, 58, 10589-10596.	1.1	67
69	Observation of Coulomb blockade oscillations in the thermopower of a quantum dot. Solid State Communications, 1993, 87, 1145-1149.	0.9	66
70	Single-electron acoustic charge transport on shallow-etched channels in a perpendicular magnetic field. Physical Review B, 2000, 62, 1564-1567.	1.1	66
71	Charging and double-frequency Aharonov-Bohm effects in an open system. Physical Review B, 1994, 49, 17456-17459.	1.1	65
72	Quantized acoustoelectric current transport through a static quantum dot using a surface acoustic wave. Physical Review B, 2003, 68, .	1.1	65

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73	Terahertz pulsed imaging as an analytical tool for sustained-release tablet film coating. European Journal of Pharmaceutics and Biopharmaceutics, 2009, 71, 117-123.	2.0	64
74	Time-of-Flight Measurements of Single-Electron Wave Packets in Quantum Hall Edge States. Physical Review Letters, 2016, 116, 126803.	2.9	64
75	One-dimensional quantised ballistic resistors in parallel configuration. Journal of Physics Condensed Matter, 1989, 1, 6763-6770.	0.7	63
76	On the acoustoelectric current in a one-dimensional channel. Journal of Physics Condensed Matter, 1996, 8, L337-L343.	0.7	63
77	Resistance resonance induced by electron-hole hybridization in a strongly coupled InAs/GaSb/AlSb heterostructure. Physical Review B, 1998, 57, 11915-11918.	1.1	62
78	Optically induced bistability in the mobility of a two-dimensional electron gas coupled to a layer of quantum dots. Applied Physics Letters, 1999, 74, 735-737.	1.5	62
79	Noise and reproducible structure in a GaAs/AlxGa1â^'xAs one-dimensional channel. Physical Review B, 1991, 44, 1938-1941.	1.1	61
80	Reentrant Insulator-Metal-Insulator Transition atB=0in a Two-Dimensional Hole Gas. Physical Review Letters, 1999, 82, 1542-1545.	2.9	60
81	Transport in a superlattice of 1D ballistic channels. Journal of Physics Condensed Matter, 1990, 2, 3405-3414.	0.7	59
82	Ballistic transport in one dimension: additional quantisation produced by an electric field. Journal of Physics Condensed Matter, 1990, 2, 7247-7254.	0.7	59
83	Influence of excess electrons and magnetic fields on Mott-Wannier excitons in GaAs quantum wells. Advances in Physics, 1995, 44, 47-72.	35.9	59
84	Coherent Time Evolution of a Single-Electron Wave Function. Physical Review Letters, 2009, 102, 156801.	2.9	59
85	Properties of a ballistic quasi-one-dimensional constriction in a parallel high magnetic field. Physical Review B, 1991, 44, 10973-10975.	1.1	58
86	Spectroscopy of a two-dimensional electron gas in the quantum-Hall-effect regime by use of low-frequency edge magnetoplasmons. Physical Review B, 1992, 46, 12427-12432.	1.1	58
87	Photoluminescence due to positively charged excitons in undoped GaAs/AlxGa1â^'xAs quantum wells. Physical Review B, 1996, 53, 13002-13010.	1.1	57
88	Coulomb interaction of two electrons in the quantum dot formed by the surface acoustic wave in a narrow channel. Physical Review B, 1999, 60, R13954-R13957.	1.1	57
89	Kondo Effect from a Tunable Bound State within a Quantum Wire. Physical Review Letters, 2008, 100, 026807.	2.9	57
90	Length Scales at the Metal-Insulator Transition in Compensated GaAs. Physical Review Letters, 1988, 61, 369-372.	2.9	55

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91	Direct experimental determination of the tunnelling time and transmission probability of electrons through a resonant tunnelling structure. Journal of Physics Condensed Matter, 1991, 2, 8969-8975.	0.7	55
92	Fabrication of high-quality one- and two-dimensional electron gases in undoped GaAs/AlGaAs heterostructures. Applied Physics Letters, 1999, 74, 2328-2330.	1.5	54
93	Direction-resolved transport and possible many-body effects in one-dimensional thermopower. Physical Review B, 2000, 62, R16275-R16278.	1.1	54
94	Chemical mapping using reflection terahertz pulsed imaging. Semiconductor Science and Technology, 2005, 20, S254-S257.	1.0	54
95	An accurate high-speed single-electron quantum dot pump. New Journal of Physics, 2010, 12, 073013.	1.2	54
96	Quantized charge pumping through a quantum dot by surface acoustic waves. Applied Physics Letters, 2004, 84, 4319-4321.	1.5	53
97	Universal conductance fluctuations and electron coherence lengths in a narrow two-dimensional electron gas. Physical Review B, 1987, 36, 4514-4517.	1.1	52
98	Possible Evidence of a Spontaneous Spin Polarization in Mesoscopic Two-Dimensional Electron Systems. Physical Review Letters, 2004, 92, 116601.	2.9	52
99	Resonant tunneling between parallel, twoâ€dimensional electron gases: A new approach to device fabrication usingin situion beam lithography and molecular beam epitaxy growth. Applied Physics Letters, 1994, 64, 1827-1829.	1.5	51
100	Wave functions and Fermi surfaces of strongly coupled two-dimensional electron gases investigated by in-plane magnetoresistance. Physical Review B, 1994, 50, 4889-4892.	1.1	51
101	Magnetization Instability in a Two-Dimensional System. Physical Review Letters, 1997, 79, 4449-4452.	2.9	51
102	Spin-dependent transport in a quasiballistic quantum wire. Physical Review B, 2000, 61, 9952-9955.	1.1	51
103	Resonant magneto-transport through a lateral quantum box in a semiconductor heterostructure. Journal of Physics Condensed Matter, 1989, 1, 6291-6298.	0.7	50
104	Experimental Evidence for Coulomb Charging Effects in an Open Quantum Dot at Zero Magnetic Field. Physical Review Letters, 1998, 81, 3507-3510.	2.9	50
105	Localisation in disordered two-dimensional systems and the universal dependence on diffusion length. Journal of Physics C: Solid State Physics, 1981, 14, L413-L419.	1.5	49
106	Effect of spatial dispersion on acoustoelectric current in a high-mobility two-dimensional electron gas. Physical Review B, 1995, 51, 14770-14773.	1.1	49
107	Weak localization in high-quality two-dimensional systems. Physical Review B, 2004, 70, .	1.1	49
108	Resonant tunneling in anAlxGa1â^'xAs/GaAs quantum dot as a function of magnetic field. Physical Review B, 1992, 46, 3948-3952.	1.1	48

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109	Spin injection between epitaxial Co2.4Mn1.6Ga and an InGaAs quantum well. Applied Physics Letters, 2005, 86, 252106.	1.5	48
110	Enhanced g factors of a one-dimensional hole gas with quantized conductance. Physical Review B, 1997, 55, R13409-R13412.	1.1	47
111	Magneto-resistance oscillations and the transition from three-dimensional to two-dimensional conduction in a gallium arsenide field effect transistor at low temperatures. Journal of Physics C: Solid State Physics, 1982, 15, L21-L30.	1.5	46
112	The growth and physics of high mobility two-dimensional hole gases. Journal of Crystal Growth, 1991, 111, 318-322.	0.7	46
113	Charging effects and the excitation spectrum of a quantum dot formed by an impurity potential. Physical Review B, 1993, 48, 8866-8871.	1.1	46
114	Bias-controlled spin polarization in quantum wires. Applied Physics Letters, 2008, 93, .	1.5	46
115	Possible observation of an electronic phase transition in Sb doped Si. Journal of Physics C: Solid State Physics, 1984, 17, L425-L432.	1.5	45
116	Enhanced current quantization in high-frequency electron pumps in a perpendicular magnetic field. Physical Review B, 2008, 78, .	1.1	45
117	Ground State of a Two-Dimensional Coupled Electron-Hole Gas inInAs/GaSbNarrow Gap Heterostructures. Physical Review Letters, 1999, 82, 2362-2365.	2.9	44
118	Spin-Incoherent Transport in Quantum Wires. Physical Review Letters, 2008, 101, 036801.	2.9	44
119	Anderson localisation of holes in a Si inversion layer. Physics Letters, Section A: General, Atomic and Solid State Physics, 1974, 48, 113-114.	0.9	43
120	Magnetic localization in silicon inversion layers. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1978, 37, 83-95.	0.6	43
121	Time-irreversible random telegraph signal due to current along a single hopping chain. Physical Review Letters, 1992, 69, 502-505.	2.9	43
122	Realization of quantum-dot cellular automata using semiconductor quantum dots. Superlattices and Microstructures, 2003, 34, 195-203.	1.4	43
123	Energy-Dependent Tunneling from Few-Electron Dynamic Quantum Dots. Physical Review Letters, 2007, 99, 156802.	2.9	43
124	The transition from two- to one-dimensional electronic transport in narrow silicon accumulation layers. Journal of Physics C: Solid State Physics, 1982, 15, L1287-L1297.	1.5	42
125	Closely separated one-dimensional wires:. Physica B: Condensed Matter, 1998, 249-251, 157-161.	1.3	42
126	Conductance quantization and the 0.7Ã—2e2â^•h conductance anomaly in one-dimensional hole systems. Applied Physics Letters, 2006, 88, 012107.	1.5	42

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127	Zero-bias anomaly in quantum wires. Physical Review B, 2009, 79, .	1.1	42
128	Quantum magnetic confinement in a curved two-dimensional electron gas. Journal of Physics Condensed Matter, 1994, 6, L127-L134.	0.7	41
129	Electric-field-induced ionization of negatively charged excitons in quantum wells. Physical Review B, 1997, 55, R1970-R1972.	1.1	41
130	Application of terahertz pulsed imaging to analyse film coating characteristics of sustained-release coated pellets. International Journal of Pharmaceutics, 2013, 457, 521-526.	2.6	41
131	Electron-electron scattering in silicon inversion layers. Journal of Physics C: Solid State Physics, 1983, 16, L353-L360.	1.5	40
132	Critical conductivity at the magnetic-field-induced metal-insulator transition in n-GaAs and n-InSb. Journal of Physics C: Solid State Physics, 1986, 19, 3983-3990.	1.5	40
133	Electron transport in a non-uniform magnetic field. Journal of Physics Condensed Matter, 1995, 7, L307-L315.	0.7	40
134	Frictional drag between parallel two-dimensional electron gases in a perpendicular magnetic field. Journal of Physics Condensed Matter, 1996, 8, L557-L562.	0.7	40
135	Parallel quantized charge pumping. Physical Review B, 2009, 80, .	1.1	40
136	Row coupling in an interacting quasi-one-dimensional quantum wire investigated using transport measurements. Physical Review B, 2009, 80, .	1.1	40
137	Fabry-Perot interferometry with electron waves. Journal of Physics Condensed Matter, 1989, 1, 9035-9044.	0.7	39
138	Aharonovâ€“Bohm effect and oneâ€dimensional ballistic transport through two independent parallel channels. Applied Physics Letters, 1993, 63, 3191-3193.	1.5	39
139	Rapid radiative decay of charged excitons. Physical Review B, 2000, 62, R13294-R13297.	1.1	39
140	Impact of long- and short-range disorder on the metallic behaviour of two-dimensional systems. Nature Physics, 2008, 4, 55-59.	6.5	39
141	The spatial extent of localized state wavefunctions in silicon inversion layers. Journal of Physics C: Solid State Physics, 1974, 7, L273-L277.	1.5	37
142	Magnetotunneling spectroscopy of one-dimensional wires. Physical Review B, 1997, 55, R1966-R1969.	1.1	37
143	Fabrication and transport properties of clean long one-dimensional quantum wires formed in modulation-doped GaAs/AlGaAs heterostructures. Applied Physics Letters, 1999, 75, 2975-2977.	1.5	37
144	Logarithmic and power law corrections in two-dimensional electronic transport. Journal of Physics C: Solid State Physics, 1982, 15, L371-L376.	1.5	36

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145	Electron-electron scattering in narrow Si accumulation layers. Journal of Physics Condensed Matter, 1989, 1, 3289-3293.	0.7	36
146	Study of the carrier density dependence of the frictional drag between closely spaced two-dimensional electron gases. Semiconductor Science and Technology, 1995, 10, 1229-1232.	1.0	36
147	Negatively charged excitons in coupled double quantum wells. Physical Review B, 1997, 55, 1318-1321.	1.1	36
148	Quantum magnetic confinement and transport in spherical two-dimensional electron gases. Physical Review B, 1995, 52, R8646-R8649.	1.1	35
149	Transport properties of two-dimensional electron gases containing InAs self-assembled dots. Applied Physics Letters, 1998, 73, 2468-2470.	1.5	35
150	Fermi-Liquid Behavior of the Low-Density 2D Hole Gas in aGaAs/AlGaAsHeterostructure at Large Values ofrs. Physical Review Letters, 2001, 86, 4895-4898.	2.9	35
151	Dephasing in an isolated double-quantum-dot system deduced from single-electron polarization measurements. Physical Review B, 2003, 67, .	1.1	35
152	Single-Electron Population and Depopulation of an Isolated Quantum Dot Using a Surface-Acoustic-Wave Pulse. Physical Review Letters, 2007, 98, 046801.	2.9	35
153	The Anderson transition in silicon inversion layers. Surface Science, 1976, 58, 79-88.	0.8	34
154	Metal-insulator transitions induced by a magnetic field. Journal of Non-Crystalline Solids, 1979, 32, 161-185.	1.5	34
155	Observation of Aharonov-Bohm oscillations in a narrow two-dimensional electron gas. Journal of Physics Condensed Matter, 1989, 1, 3369-3373.	0.7	34
156	Quantized current in one-dimensional channel induced by surface acoustic waves. Physica B: Condensed Matter, 1998, 249-251, 140-146.	1.3	34
157	A metal-insulator transition in the impurity band of n-type GaAs induced by loss of dimension. Journal of Physics C: Solid State Physics, 1977, 10, L173-L177.	1.5	33
158	Experimental investigation of the surface acoustic wave electron capture mechanism. Physical Review B, 2006, 74, .	1.1	33
159	Electrons in one dimension. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2010, 368, 1141-1162.	1.6	33
160	Spin-orbit coupling and weak localisation in the 2D inversion layer of indium phosphide. Journal of Physics C: Solid State Physics, 1982, 15, L1137-L1145.	1.5	32
161	An experimental test of the scaling theory of conduction in two dimensions. Journal of Physics C: Solid State Physics, 1983, 16, L285-L289.	1.5	32
162	Backâ€gated splitâ€gate transistor: A oneâ€dimensional ballistic channel with variable Fermi energy. Applied Physics Letters, 1992, 60, 2782-2784.	1.5	32

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163	A new mechanism for high-frequency rectification in a ballistic quantum point contact. Journal of Physics Condensed Matter, 1994, 6, L163-L168.	0.7	32
164	Energy-level pinning and the 0.7 spin state in one dimension: GaAs quantum wires studied using finite-bias spectroscopy. Physical Review B, 2007, 75, .	1.1	32
165	The observation of localisation and interaction effects in the two-dimensional electron gas of a GaAs-GaAlAs heterojunction at low temperatures. Journal of Physics C: Solid State Physics, 1981, 14, L995-L1005.	1.5	31
166	Electronic instabilities in the hot-electron regime of the one-dimensional ballistic resistor. Journal of Physics Condensed Matter, 1989, 1, 6285-6290.	0.7	31
167	Experimental study of the acoustoelectric effects in GaAs-AlGaAs heterostructures. Journal of Physics Condensed Matter, 1995, 7, 7675-7685.	0.7	31
168	Magnetic separation of localisation and interaction effects in a two-dimensional electron gas at low temperatures. Journal of Physics C: Solid State Physics, 1981, 14, L531-L537.	1.5	30
169	The frequency effect and the quantised Hall resistance. Journal of Physics C: Solid State Physics, 1983, 16, L113-L117.	1.5	30
170	The Aharonov-Bohm effect in the fractional quantum Hall regime. Surface Science, 1996, 361-362, 17-21.	0.8	30
171	Fractional quantum Hall effect in bilayer two-dimensional hole-gas systems. Physical Review B, 1996, 54, R5259-R5262.	1.1	30
172	Metallic Behavior in Dilute Two-Dimensional Hole Systems. Physical Review Letters, 2001, 87, 126802.	2.9	30
173	Conductance oscillations in a two-dimensional impurity band. Journal of Physics C: Solid State Physics, 1979, 12, L617-L625.	1.5	29
174	The magnetic field induced metal-insulator transition in n-type InP. Journal of Physics C: Solid State Physics, 1984, 17, 3391-3400.	1.5	29
175	Distribution-function analysis of mesoscopic hopping conductance fluctuations. Physical Review B, 1996, 54, 2091-2100.	1.1	29
176	Ultrafast voltage sampling using single-electron wavepackets. Applied Physics Letters, 2017, 110, .	1.5	29
177	Spin-dependent and localisation effects at Si/SiO2device interfaces. Semiconductor Science and Technology, 1989, 4, 1045-1060.	1.0	28
178	Resonant transmission through an open quantum dot. Physical Review B, 1997, 55, 6723-6726.	1.1	28
179	All-Electrical Injection and Detection of a Spin-Polarized Current Using 1D Conductors. Physical Review Letters, 2012, 109, 177202.	2.9	28
180	One-dimensional ballistic resistor in hot-electron regime: nonlinear and negative differential resistance to 10 THz. Electronics Letters, 1989, 25, 992.	0.5	27

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181	Electron-density-dependent optical spectra of a remotely-doped GaAs/Al0.33Ga0.67As single quantum well. Superlattices and Microstructures, 1994, 15, 355.	1.4	27
182	Fabrication of high mobilityin situback-gated (311)A hole gas heterojunctions. Applied Physics Letters, 1997, 70, 2750-2752.	1.5	27
183	Excitonic recombination processes in spin-polarized two-dimensional electron gases. Physical Review B, 1998, 58, R4227-R4230.	1.1	27
184	Influence of parallel magnetic fields on a single-layer two-dimensional electron system with a hopping mechanism of conductivity. Physical Review B, 2000, 61, 7253-7256.	1.1	27
185	0.7 Structure and Zero Bias Anomaly in Ballistic Hole Quantum Wires. Physical Review Letters, 2008, 100, 016403.	2.9	27
186	LO-Phonon Emission Rate of Hot Electrons from an On-Demand Single-Electron Source in a GaAs/AlGaAs Heterostructure. Physical Review Letters, 2018, 121, 137703.	2.9	27
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